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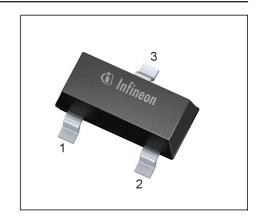






Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain broadband amplifiers at collector currents from 2 mA to 30 mA
- f_T = 8 GHz, NF_{min} = 0.9 dB at 900 MHz
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFR183	RHs	1=B	2=E	3=C	SOT23

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I _C	65	mA
Base current	l _B	5	
Total power dissipation ¹⁾	P _{tot}	450	mW
T _S ≤ 60 °C			
Junction temperature	T_{J}	150	°C
Storage temperature	T_{Stg}	-55 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	200	K/W

1

 $^{{}^1}T_{\rm S}$ is measured on the collector lead at the soldering point to the pcb

 $^{^2}$ For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V _{(BR)CEO}	12	-	-	V
$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$, ,				
Collector-emitter cutoff current	I _{CES}	-	_	100	μΑ
$V_{CE} = 20 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB} = 10 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I _{EBO}	-	-	1	μΑ
$V_{\rm EB} = 1 \text{ V}, I_{\rm C} = 0$					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, pulse measured					



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

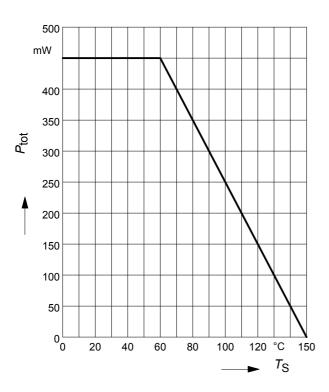
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling	g)	,			
Transition frequency	f_{T}	6	8	-	GHz
$I_{\rm C}$ = 25 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz					
Collector-base capacitance	C _{cb}	-	0.37	0.57	pF
$V_{\text{CB}} = 10 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,					
emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.2	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C _{eb}	-	1.1	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,					
collector grounded					
Minimum noise figure	NF _{min}				dB
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 900 MHz		-	0.9	-	
f = 1.8 GHz		-	1.4	_	
Power gain, maximum stable ¹⁾	G _{ms}	-	17.5	-	dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 900 MHz					
Power gain, maximum available ¹⁾	G _{ma}	-	11.5	-	dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 1.8 GHz					
Transducer gain	S _{21e} ²				dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz		-	14.5	_	
f = 1.8 MHz		_	9	_	

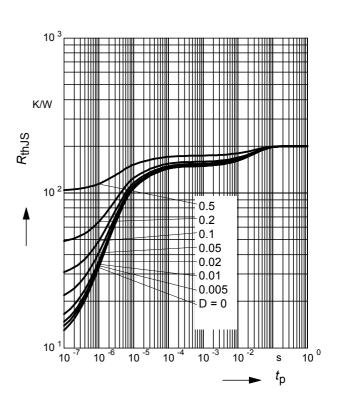
 $^{^{1}}G_{\mathsf{ma}} = |S_{21e} \, / \, S_{12e}| \; (\mathsf{k}\text{-}(\mathsf{k}^{2}\text{-}1)^{1/2}), \; G_{\mathsf{ms}} = |S_{21} \, / \, S_{12}|$



Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$

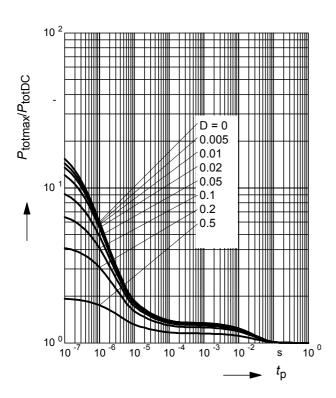
Permissible Pulse Load $R_{thJS} = f(t_p)$





Permissible Pulse Load

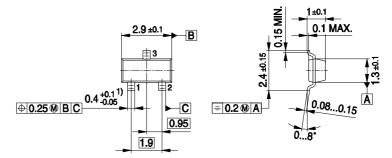
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$$





Package Outline

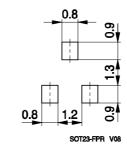




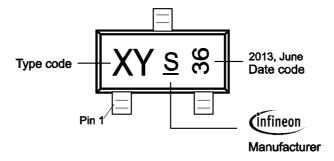
1) Lead width can be 0.6 max. in dambar area

SOT23-PO V08

Foot Print

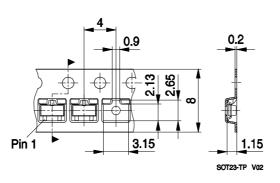


Marking Layout



Standard Packing

Reel o 180 mm: 3.000 Pieces / Reel Reel o 330 mm = 10.000 Pieces / Reel



5



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6